Structure and stability of cluster-assembled solid Al₁₂C(Si): A first-principles study

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We have proposed a possible crystal structure for the cluster-assembled solid $Al_{12}C(Si)$, and its electronic structures and stability have been studied in the framework of density functional theory and *ab initio* molecular dynamics. We find that $Al_{12}C(Si)$ clusters are condensed by van der Waals force, with a very small cohesive energy of ~ 1.1 eV. The combined steepest descent on ions shows that upon the formation of solid the relaxation of atomic distances in the $Al_{12}C(Si)$ cluster is very small. The stability of the $Al_{12}C(Si)$ solid is also confirmed by a dynamical simulation at low temperature. [S0163-1829(97)02427-2]

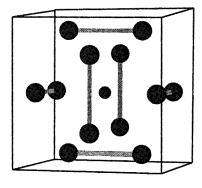
In the past decades, a great deal of effort has been devoted to the synthesizing and the fundamental understanding of new materials in an atomic dimension. With the discovery of the C₆₀ molecule and its solid phase,² an enormous interest in the study of cluster and cluster-assembled materials has been aroused. Since the properties of clusters are quite different from that of atoms, it is reasonable to expect that the cluster-assembled materials have unusual properties, which would be quite different from that in the atomic solid phase, like what was observed in solid C₆₀. Generally to synthesize a cluster-assembled solid, stable cluster, as the building block of the solid, is necessary, and also the interaction between the clusters should be much smaller than the interaction in the cluster. Otherwise when the clusters are brought together, the structure of cluster would coalesce to form another phase. Moreover, since the cluster is not completely spherical-like, the geometric effects can play a crucial role on the formation of the cluster-assembled solid.

Recently, from the total energy and electronic structure calculations, 4 it had been found that the stability of Al₁₃ cluster can be significantly enhanced by doping with a tetravalent carbon atom. Since there exists about a 2 eV gap between the highest occupied molecular orbitals (HOMO) and the lowest unoccupied molecular orbitals (LUMO), the interaction between the Al₁₂C(Si) cluster can be expected to be small. Therefore the Al₁₂C(Si) cluster is suggested to be a good candidate to form a cluster-assembled solid. In fact, the high stability of Al₁₂C cluster was confirmed by a few recent studies.^{5,6} Seitsonen et al.⁶ studied the dynamical stability of Al₁₂C cluster by the Car-Parrinello method, and they found that, even above 900 K, the structure of Al₁₂C cluster remains icosahedral-like, which indicates that the Al₁₂C cluster is indeed stable. Moreover, Kawai⁵ has studied the interaction between two Al₁₂C clusters by the Car-Parrinello method, they found that the structure of Al₁₂C clusters remains unchanged. However no successful studies for the cluster-assembled Al₁₂C solid have been made. Seitsonen et al.6 studied the properties of Al₁₂C solid with the fcc-like structure, but they found that the total energies increased monotonically with the decreasing of the lattice constant, and there is no local minimum which is necessary for the formation of a metastable phase. For the Al₁₂Si solid with fcc-like structure, a very short Al-Al bond length between clusters¹² is found, its bond energy was even larger than that in the Al bulk. So obviously the fcc-like Al₁₂Si solid would also not be stable, since the structure of icosahedral Al₁₂Si cluster would coalesce.

As discussed by Khannan and Jena, the geometric effects are important in the cluster-assembled materials. In the icosahedral $Al_{12}C(Si)$ cluster, although 12 aluminum atoms are homogeneously distributed on a spherical surface, it cannot be rotational invariant like a rare-gas atom. It is well known that, even in the icosahedral fullerene of C_{60} , which has a smoother surface since it contains 60 carbon atoms on the surface, various phases with different rotational order have been observed at low temperature. Obviously, the relative orientation of clusters may play an important role in the formation of a solid from the icosahedral $Al_{12}C(Si)$ clusters.

In this paper, based on the limited search in the configuration space, we propose a crystal structure for the cluster-assembled $Al_{12}C(Si)$ solid. In the total energy calculations, we have obtained an energy minimum and we do find that the interaction between the clusters in $Al_{12}C(Si)$ solid is very weak, and the cohesive energy is very small. By performing the combined steepest descent on the ions and electrons, and the dynamical simulation at low temperature, we show that the $Al_{12}C$ solid is a stable van der Waals solid.

The recent simulations on the cluster dimer (two icosahedral 13-atom clusters) with the Leonard-Jones potential show that, the relative cluster orientation is very important for the stability of the cluster dimer. If we put 12 surface atoms of a body-center icosahedron on the six faces of a cubic box, the most stable structure for a cluster dimer is with two cubic boxes in alternated orientation of 90°, as shown in Fig. 1. In fact, only in this configuration, the mass centers of two icosahedrons can be approached more closely than any other isomers which have higher energies, as confirmed by the charge density shown below. This suggests that, when the clusters are brought together, they should be properly arranged according to their geometric shape. In fact, the intuitive fcc-like structure, which is the lowest energy structure for the atomic van der Waals solid, was proved to be unstable for cluster-assembled Al₁₂C solid and Al₁₂Si solid. So, we have tried to design a structure for Al₁₂C(Si) solid, in



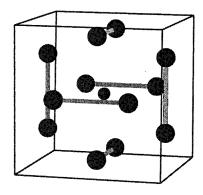


FIG. 1. The atomic structure of $Al_{12}C$ cluster dimer, and the relative orientation of $Al_{12}C$ clusters in solid phase. Big balls for Al atoms and small balls for C atoms.

which each Al₁₂C(Si) cluster is alternated 90° with all its nearest neighbors. This turns out to be a cubiclike crystal structure, each unit cell contains eight Al₁₂C(Si) clusters. Actually, a similar structure has been observed in AB_{13} system, 10 where B_{13} has an icosahedral structure, the large atom A is believed to be an electron donor to close the electronic shell of B_{13} which makes B_{13} stable. To show whether this structure is stable for Al₁₂C solid, we have performed a first-principles calculation and ab-initio moleculardynamics simulation, and its stability is confirmed. With the same crystal structure, we have studied the properties of the cluster-assembled solid Al₁₃K, which was suggested to have a CsCl structure, 13 but recent calculation showed that an icosahedral Al₁₃K cluster would not be stable in CsCl structure.¹⁴ The results on Al₁₃K will be published elsewhere.

All our calculations are based on the density functional theory with the local density approximation¹⁵ and Car-Parrinello method. 16 The electronic density is expressed in terms of Kohn-Sham orbitals,¹⁷ which are expanded into plane waves with an energy cutoff of 35 Ry for carbon and 14 Ry for silicon. Only the valence electrons are treated explicitly and their interactions with the ionic cores are de-Bachelet-Hamann-Schluter by the pseudopotentials 18 with sp nonlocality. The minimization of the energy functional is performed with a conjugate gradient for the fixed atomic distances and is also combined with the steepest descent for electrons and ions in Al₁₂C solid at a lattice constant of 30.8 a.u. We have used a time step of 4.0 a.u. and fictitious mass of 300 a.u. for electrons in all the calculations.

First, we have calculated the equilibrium structure for the isolated Al₁₂C and Al₁₂Si cluster. Since our method is based on the plane wave, it is necessary to use the periodical boundary condition. To erase the interaction between the cluster and its images, one need to use a big unit cell. The test shows that a fcc-like unit cell with a lattice constant of 33 a.u. is enough to make the interaction negligible. By calculating the binding energies at various atomic distances, the obtained equilibrium distances are 4.66 a.u. and 4.89 a.u. for Al-C and Al-Si bonds, respectively, which is the same as the result obtained by Seitsonen *et al.*, ^{6,12} but it is smaller than the previous results obtained by other ab initio methods with a localized basis function.4 We have obtained binding energies of 45.9 eV and 44.7 eV for an isolated Al₁₂C and Al₁₂Si cluster, respectively, which are very close Seitsonen's results. These results are also in agreement with the results of other previous ab initio methods. 19 As we can see from Table I, it seems that the calculations based on atomic orbitals give systematically larger atomic distances compared with the results from pseudopotentials. But the difference of bond lengths between Al₁₂Si cluster and Al₁₂C cluster is consistent with the pseudopotential's results. It is also worth noting that the binding energies of the Al₁₂Si cluster and Al₁₂C cluster are very close in various calculations. Since the atomic size of the silicon atom is larger than the carbon atom, the obtained Al-Si bond length is also larger than the Al-C bond length.

To calculate the cohesive energy of $Al_{12}C(Si)$ solids with the structure presented above, we have used a primitive cell with two $Al_{12}C(Si)$ clusters. The obtained total energies via the lattice constant, relative to the isolated clusters, are

TABLE I. Comparison of the binding energy (E_b) and the nearest neighbor distance for icosahedral $Al_{12}Si$ and $Al_{12}C$ clusters.

	$\mathrm{Al}_{12}\mathrm{Si}$		$Al_{12}C$	
	d(Al-Si) (a.u.)	E_b (eV)	d(Al-C) (a.u.)	E_b (eV)
Present ^a	4.89	44.7	4.68	45.9
Seitsonen et al. b	4.89	44.9	4.69	45.3
Gong and Kumar c	5.22	39.2	5.05	40.6
Khanna and Jena c	5.05	39.2	4.78	41.1

aSee, also, Ref. 2.

^bReferences 6 and 12.

^cReference 4.

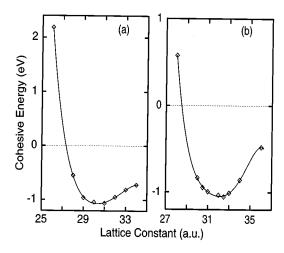


FIG. 2. The cohesive energies for the cluster-assembled $Al_{12}C(Si)$ solids. The solid line is the guide for the eye. The left panel for the $Al_{12}C$ solid and the right panel for the $Al_{12}Si$ solid.

shown in Fig. 2. In contrary to the result of the fcc-like solid, we have obtained an energy minimum at the lattice constant \sim 30.8 a.u. and \sim 32.5 a.u. for the Al₁₂C solid and Al₁₂Si solid, respectively, which indicates that the Al₁₂C(Si) solid could be formed with this lattice constant. The very small cohesive energy of ~ 1.1 eV, which is comparable to ~ 1.6 eV for the C_{60} solid,³ implies that the $Al_{12}C(Si)$ clusters are condensed by a rather weak van der Waals force. Similar to the C₆₀ solid in which intracluster C-C distance is almost twice the intercluster C-C distance, the shortest Al-Al distance between different clusters in the Al₁₂C(Si) solid is about 9.2 a.u. (9.9 a.u.), which is much longer than the normal Al-Al bond in bulk aluminum, therefore it is very difficult for Al atoms from different clusters to have a stronger interaction than the van der Waals interaction. These features are also visible in the contour map of the valence charge density. Figure 3 shows the charge density of Al₁₂C. In fact, the main feature in the charge density of Al₁₂Si is very simi-

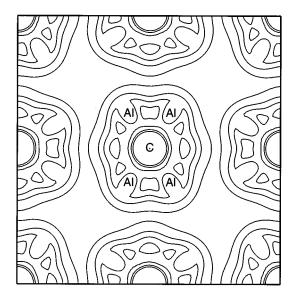


FIG. 3. The contour map of charge density on (001) plan for $Al_{12}C$.

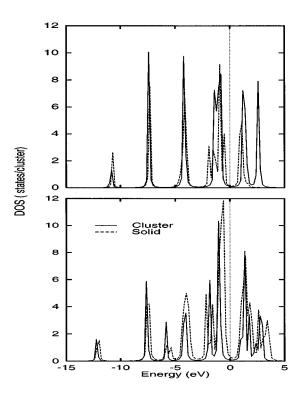


FIG. 4. The electronic density of states for cluster-assembled solids (solid line) and clusters (dash line). The up panel for $Al_{12}Si$ and the lower panel for $Al_{12}C$.

lar to what observed in $Al_{12}C$. From Fig. 3 we can see that the charge density of $Al_{12}C$ cluster in solid is almost the same as the charge density of the isolated cluster, and the charge density overlap between the clusters is very small leading to a stable cluster-assembled solid. It is worth noting that the charge density of $Al_{12}C$ cluster (visible from Fig. 3) is not spherical-like. At one axis direction, the charge density has a tendency to move inwards to the center of carbon, and at another axis direction, the charge density has a tendency to move outwards from the center of carbon. So the neighboring clusters need to rotate 90° in order to bring them closer without distorting the charge density significantly. While in fcc-like $Al_{12}C(Si)$ solid, these *inwards* and *outwards* features in charge density cannot be well matched. This may be one of the reasons why the fcc-like $Al_{12}C(Si)$ solid is not stable.

At the equilibrium lattice constants, which corresponds to the energy minimum in Fig. 2, we have calculated the total energies by changing the atomic distances in the clusters. We find that changes for Al-C(Si) bonds are very small. Then when we have performed the combined steepest descent on ions and electrons, a very small relaxation on the structure has been observed again with the energy gaining only about $0.02~{\rm eV}$. These results clearly indicate that the icosahedral structure of the isolated ${\rm Al}_{12}{\rm C(Si)}$ cluster remains unchanged upon forming a solid, and it is stable against the steepest descent.

The electronic density of states is obtained by the Lorentz expansion of Kohn-Sham eigenvalues. Figure 4 shows the obtained results for the isolated clusters and also for the solids. We can see that the basic features of the density of states for the cluster and solid are almost the same. The small splitting of degenerate states in solid, which is generally propor-

tional to the crystal field, confirms again the very weak interaction between the clusters in $Al_{12}C(Si)$ solid. For the isolated cluster, we have obtained a HOMO-LUMO gap up to 1.96 eV, which is close to the results obtained in the previous calculation by the discrete variational method.⁴ In the solid, we find that the change of gap due to the dispersion is small, the obtained energy gap for $Al_{12}C$ solid is 1.52 eV, and for $Al_{12}Si$ is 1.41 eV, which is almost the same as the result obtained for C_{60} solid.³

To further check the stability of $Al_{12}C$ solid, we have performed a molecular-dynamics simulation at a temperature of $\sim\!20$ K. The simulation is started by giving a small random displacement to each of atoms at the equilibrium structure with a lattice constant of 30.8 a.u. Contrary to the result of fcc-like $Al_{12}C$ (and also $Al_{12}Si$) solid, 6,12 we find that the structure of icosahedral $Al_{12}C$ cluster remains unchanged in our observed time of 1.1 ps. The atoms move only around the equilibrium positions. It will also be very interesting to study its dynamical properties and stability changing with temperature, and with pressure, since it may probably have another phase by applying a certain pressure as observed in a typical molecular solid, 20 this work is still in progress.

In conclusion, we have proposed a possible structure for the cluster-assembled Al₁₂C(Si) solid. Based on the firstprinciples methods, its stability is confirmed by a cohesive energy, steepest descent on the ions and a dynamical simulation at low temperature. The very small cohesive energy and the small overlap of charge density between clusters suggest that the forces between the $Al_{12}C(Si)$ clusters in the solid phase is van der Waals like. The obtained physical properties for both $Al_{12}C$ solid and $Al_{12}Si$ solid, like electronic structures, are similar to C_{60} solid, which indicates that the $Al_{12}C(Si)$ solid might be another interesting cluster-assembled solid. However, since our search in the configuration space is limited, we cannot be sure that this structure for the $Al_{12}C(Si)$ is the most stable. The present studies also show that the shape and geometric structure of the cluster can play an important role in synthesizing a solid, which may bring very rich structures to the cluster-assembled solid.

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